

Silicon PNP Power Transistors

2N6594

DESCRIPTION

- With TO-3 package
- Complement to type 2N6569
- Wide area of safe operation

APPLICATIONS

- Designed for low voltage amplifier power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

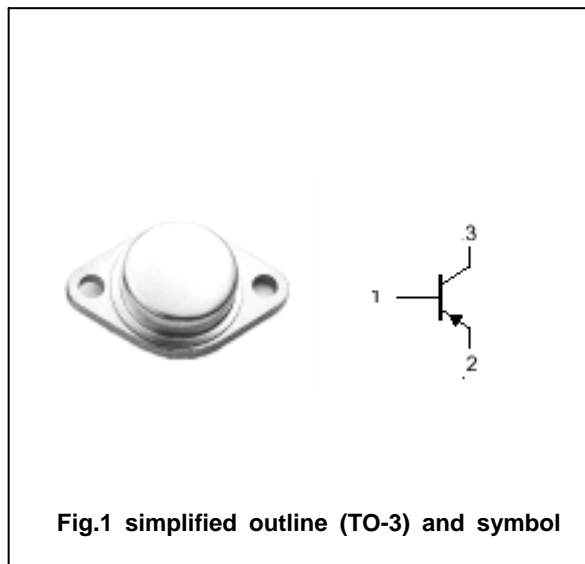


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-45	V
V _{CEO}	Collector-emitter voltage	Open base	-40	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-12	A
I _{CM}	Collector current-peak		-24	A
I _B	Base current		-5	A
I _E	Emitter current		-17	A
I _{EM}	Emitter current-peak		-34	A
P _C	Collector power dissipation	T _C =25	100	W
T _j	Junction temperature		200	
T _{stg}	Storage temperature		-65~200	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.1A ; I _B =0	-40			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.4A			-1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-12A; I _B =-2.4A			-4.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-4A; I _B =-0.4A			-2.0	V
I _{CEO}	Collector cut-off current	V _{CE} =-40V; I _B =0			-1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =-45V; I _E =0			-1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-5.0	mA
h _{FE-1}	DC current gain	I _C =-4A ; V _{CE} =-3V	15		200	
h _{FE-2}	DC current gain	I _C =-12A ; V _{CE} =-4V	5		100	
f _T	Transition frequency	I _C =-1.0A ; V _{CE} =-4V; f=0.5MHz	1.5		20	MHz

Switching times

t _d	Delay time	I _C =-2A; I _{B1} =-I _{B2} =-0.2A V _{CC} =-30V; t _p =25 μ s; Duty Cycle 2.0%			0.4	μ s
t _r	Rise time				1.5	μ s
t _{stg}	Storage time				5.0	μ s
t _f	Fall time				1.5	μ s

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.75	/W

